

Silicon NPN Power Transistors

2SD1562 2SD1562A

DESCRIPTION

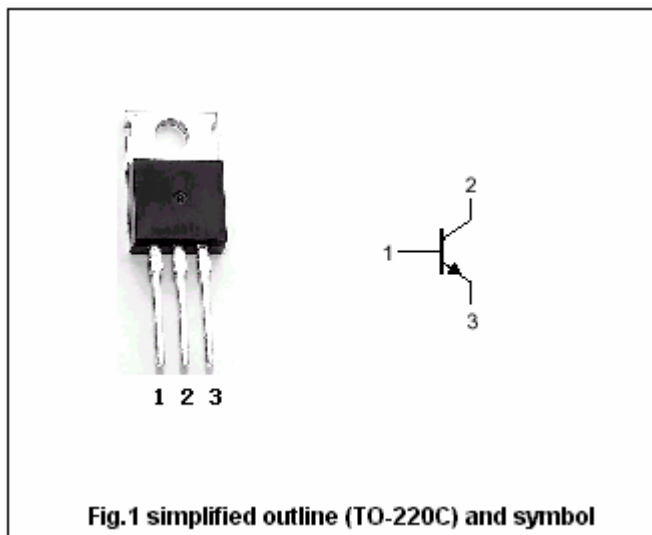
- With TO-220C package
- Complement to type 2SB1085/1085A
- High transition frequency

APPLICATIONS

- For low frequency power amplifier applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



Absolute maximum ratings(Tc=25 )

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	2SD1562	120	V
		2SD1562A	160	
V <sub>CEO</sub>	Collector-emitter voltage	2SD1562	120	V
		2SD1562A	160	
V <sub>EBO</sub>	Emitter-base voltage	Open collector	5	V
I <sub>C</sub>	Collector current		1.5	A
I <sub>CM</sub>	Collector current-peak		3.0	A
P <sub>C</sub>	Collector power dissipation	T <sub>C</sub> =25	20	W
		T <sub>a</sub> =25	1.5	
T <sub>j</sub>	Junction temperature		150	
T <sub>stg</sub>	Storage temperature		-55~150	

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## CHARACTERISTICS

T<sub>j</sub>=25 unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	2SD1562	I <sub>C</sub> =1mA; I <sub>B</sub> =0	120			V
		2SD1562A		160			
V <sub>(BR)CBO</sub>	Collector-base breakdown voltage	2SD1562	I <sub>C</sub> =50 μ A; I <sub>E</sub> =0	120			V
		2SD1562A		160			
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage		I <sub>E</sub> =50 μ A; I <sub>C</sub> =0	5			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage		I <sub>C</sub> =1 A; I <sub>B</sub> =0.1 A			2.0	V
V <sub>BEsat</sub>	Base-emitter on saturation voltage		I <sub>C</sub> =1 A; I <sub>B</sub> =0.1 A			1.5	V
I <sub>CBO</sub>	Collector cut-off current		V <sub>CB</sub> =120V; I <sub>E</sub> =0			1.0	μ A
I <sub>EBO</sub>	Emitter cut-off current		V <sub>EB</sub> =4V; I <sub>C</sub> =0			1.0	μ A
h <sub>FE</sub>	DC current gain	2SD1562	I <sub>C</sub> =0.1A; V <sub>CE</sub> =5V	60		320	
		2SD1562A		60	200		
f <sub>T</sub>	Transition frequency		I <sub>E</sub> =-0.1A; V <sub>CE</sub> =5V		80		MHz
C <sub>OB</sub>	Output capacitance		I <sub>E</sub> =0; V <sub>CB</sub> =10V; f=1MHz		20		pF

◆ h<sub>FE</sub> classifications

TYPE	D	E	F
2SD1562	60-120	100-200	160-320
2SD1562A	60-120	100-200	

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PACKAGE OUTLINE

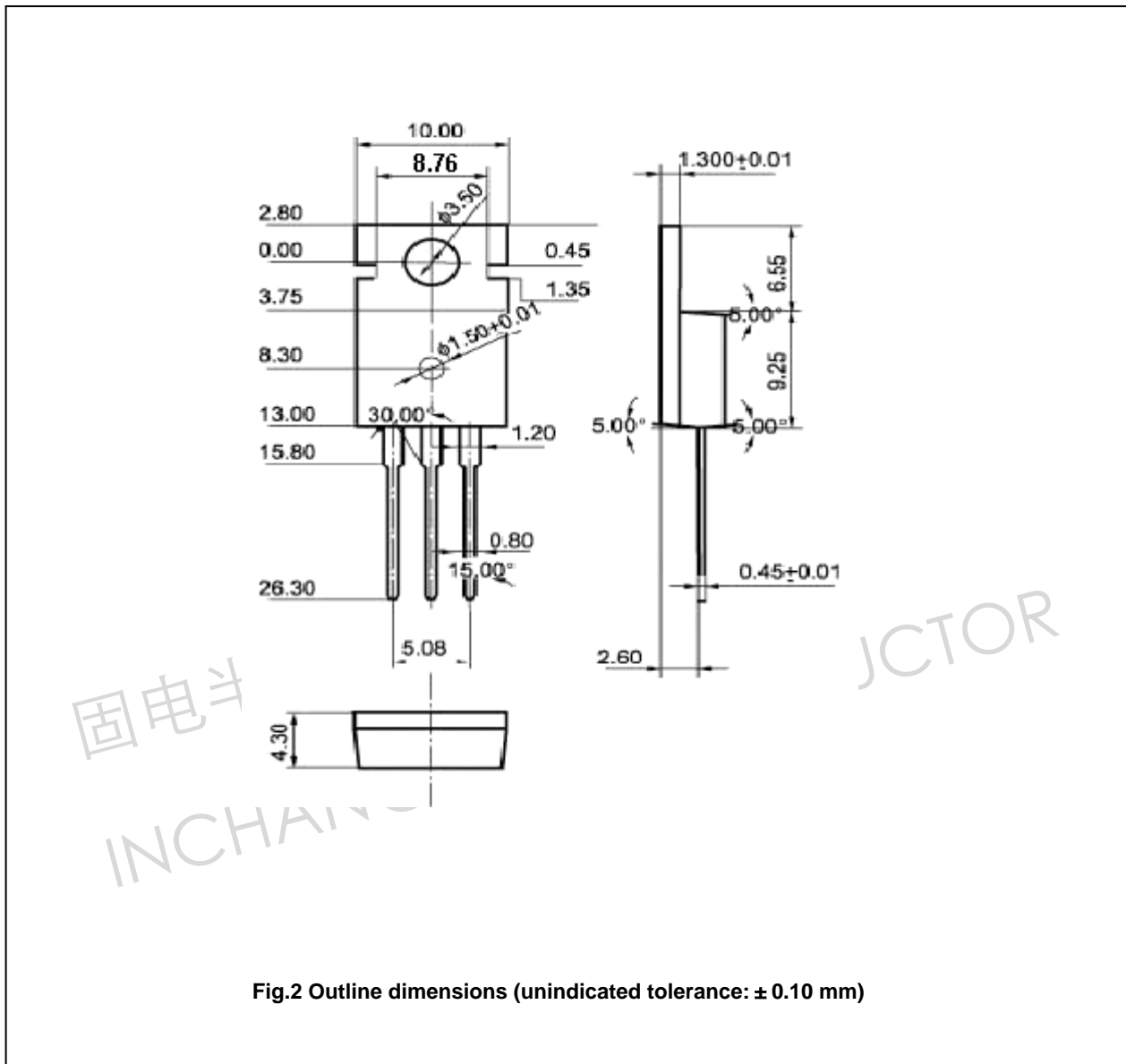


Fig.2 Outline dimensions (unindicated tolerance:  $\pm 0.10$  mm)